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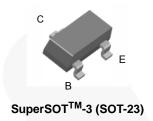
September 2015



FSB619 NPN Low-Saturation Transistor

Features

• This device is designed with high-current gain and low-saturation voltage with collector currents up to 3 A continuous.



Ordering Information

Part Number Marking		Package	Packing Method	
FSB619	619	SSOT 3L	Tape and Reel	

Absolute Maximum Ratings(1),(2)

Stresses exceeding the absolute maximum ratings may damage the device. The device may not function or be operable above the recommended operating conditions and stressing the parts to these levels is not recommended. In addition, extended exposure to stresses above the recommended operating conditions may affect device reliability. The absolute maximum ratings are stress ratings only. Values are at $T_A = 25^{\circ}$ C unless otherwise noted.

Symbol	Parameter	Value	Unit
V _{CEO}	Collector-Emitter Voltage	50	V
V _{CBO}	Collector-Base Voltage	50	V
V _{EBO}	Emitter-Base Voltage	5	V
۱ _C	Collector Current - Continuous	2	А
T _J , T _{STG}	Operating and Storage Junction Temperature Range	-55 to +150	°C

Notes:

- 1. These ratings are based on a maximum junction temperature of 150°C.
- 2. These are steady-state limits. Fairchild Semiconductor should be consulted on applications involving pulsed or low-duty-cycle operations.

Thermal Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Max.	Unit
P _D	Total Device Dissipation ⁽³⁾	500	mW
	Derate Above 25°C	4	mW/°C
R _{θJA}	Thermal Resistance, Junction-to-Ambient	250	°C/W

Note:

3. Device mounted on FR-4 PCB 4.5" X 5"; mounting pad 0.02 in² of 2oz copper.

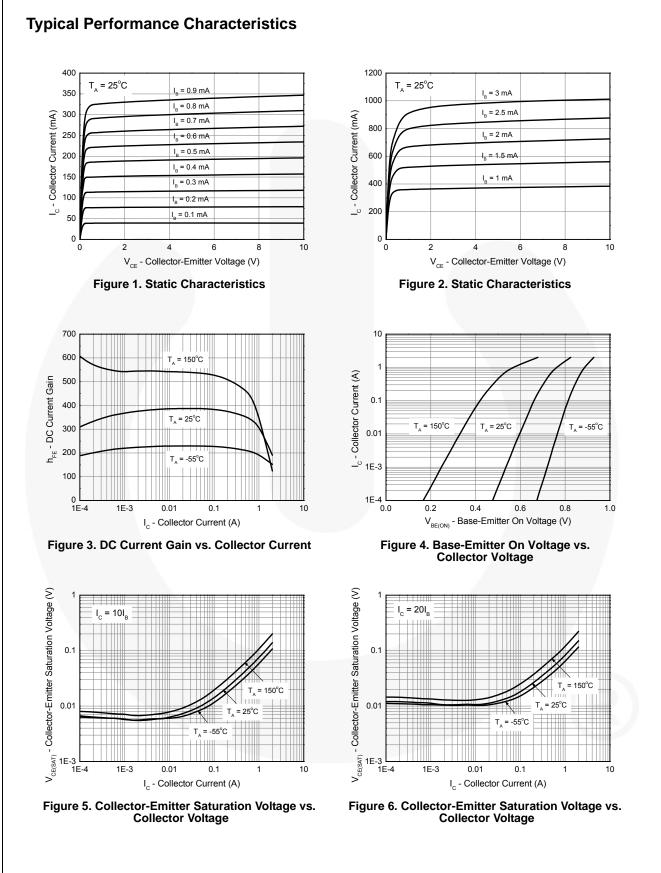
Electrical Characteristics

Values are at $T_A = 25^{\circ}C$ unless otherwise noted.

Symbol	Parameter	Conditions	Min.	Max.	Unit
BV _{CEO}	Collector-Emitter Breakdown Voltage	I _C = 10 mA, I _B = 0	50		V
BV _{CBO}	Collector-Base Breakdown Voltage	I _C = 100 μA, I _E = 0	50		V
BV _{EBO}	Emitter-Base Breakdown Voltage	I _E = 100 μA, I _C = 0	5		V
I _{CBO}	Collector Cut-Off Current	V _{CB} = 40 V, I _E = 0		100	nA
I _{EBO}	Emitter Cut-Off Current	V _{EB} = 4 V, I _C = 0		100	nA
I _{CES}	Collector Emitter Cut-Off Current	V _{CES} = 40 V		100	nA
	DC Current Gain ⁽⁴⁾	I _C = 10 mA, V _{CE} = 2 V	200		
h _{FE}		I _C = 200 mA, V _{CE} = 2 V	300		
		I _C = 1 A, V _{CE} = 2 V	200		
		I _C = 2 A, V _{CE} = 2 V	100		
V _{CE} (sat)	Collector-Emitter Saturation	I _C = 100 mA, I _B = 10 mA		20	
		I _C = 1 A, I _B = 10 mA		235	mV
	Vollage	I _C = 2 A, I _B = 50 mA		320	
V _{BE} (sat)	Base-Emitter Saturation Voltage ⁽⁴⁾	I _C = 2 A, I _B = 50 mA		1	V
V _{BE} (on)	Base-Emitter On Voltage ⁽⁴⁾	I _C = 2 A, V _{CE} = 2 V		1	V
C _{obo}	Output Capacitance	V _{CB} = 10 V, I _E = 0, f = 1 MHz		30	pF
f _T	Transition Frequency	I _C = 50 mA, V _{CE} = 10 V, f = 100 MHz	100		

Note:

4. Pulse test: pulse width \leq 300 µs, duty cycle \leq 2.0%



© 1998 Fairchild Semiconductor Corporation FSB619 Rev. 2.2 Typical Performance Characteristics (Continued) 10 Base-Emitter Saturation Voltage (V) = 201 $T_A = -55^{\circ}C$ T, = 25°C $T_{A} = 150^{\circ}C$ V BE(SAT) -0.1 1 10 1E-4 1E-3 0.01 0.1 1 10 I_c - Collector Current (A) I - Collector Current (A) Figure 7. Base-Emitter Saturation Voltage vs. Collector Current Figure 8. Base-Emitter Saturation Voltage vs. Collector Current 1000 Emitter Cut-Off Current (nA) 100 $T_{A} = 150^{\circ}C$ 10 1 0.1 0.01 T_A = 25°C T_≜ = -55°C EBO -1E-3 1E-4 50 60 2 3 4 5 6 V_{EB} - Emitter-Base Voltage (V) V_{CB} - Collector-Base Voltage (V) Figure 9. Collector Cut-Off Current vs. Collector-Base Voltage Figure 10. Emitter Cut-Off Current vs. Emitter-Base Voltage 100 90 80 f = 1 MHz Level = 40 mV 70 C_{ob} - Output Capacitance (pF) $T_A = 25^{\circ}C$ 60 50 40 30 20 10 L 0.1 10 100 10 V_{CB} - Collector-Base Voltage (V) V_{FB} - Emitter-Base Voltage (V) Figure 11. Typical Input Capacitance Figure 12. Typical Output Capacitance

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10

= 101

T_A = -55°C

T_A = 150°C

0.01

T₄ = 150°C

T₄ = 25°C

T_A = -55°C

40

30

1E-3

T, = 25°C

0.1

 $V_{\text{BE(SAT)}}$ - Base-Emitter Saturation Voltage (V) 1 10

1E-4

1000

100

10

1

0.1

0.01

1E-3

1000 900 800

700

600

500

400 300

200

100 L 0.1

C_{IB} - Input Capacitance (pF)

10

20

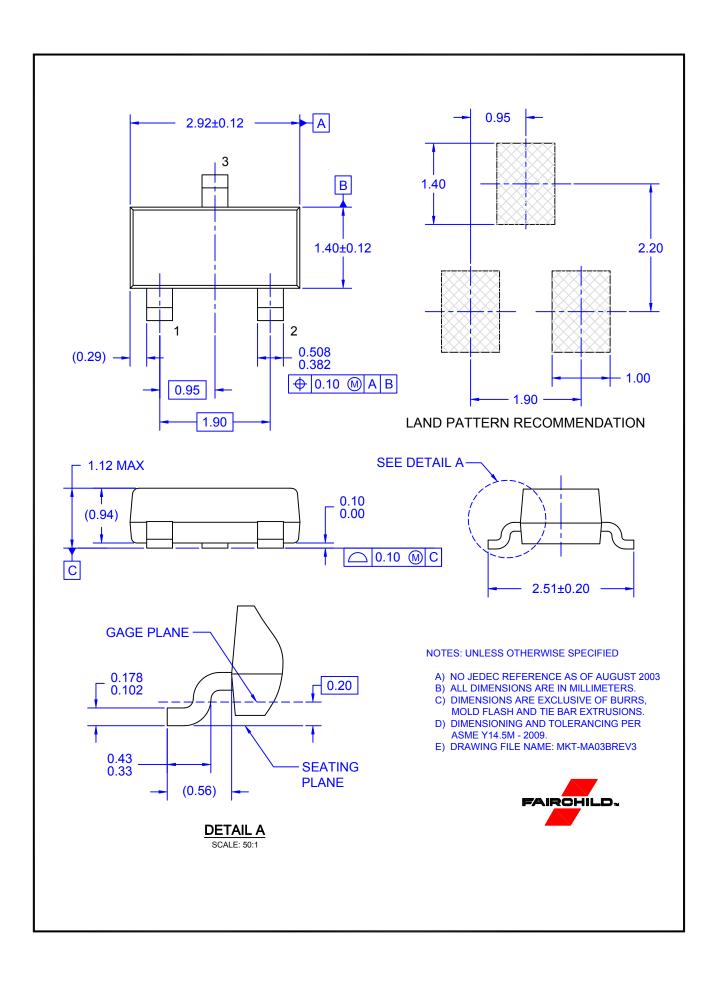
f = 1 MHz

T_A = 25°C

Level = 40 mV

- Collector Cut-Off Current (nA)

FSB619 — NPN Low-Saturation Transistor



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